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## 2N4401 / MMBT4401 NPN General-Purpose Amplifier

### Description

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.

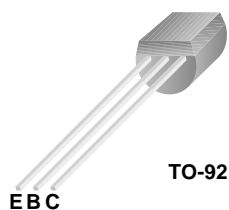


Figure 1. 2N4401 Device Package

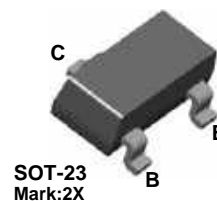


Figure 2. MMBT4401 Device Package

### Ordering Information

Part Number	Marking	Package	Packing Method
2N4401BU	2N4401	TO-92 3L	Bulk
2N4401TF	2N4401	TO-92 3L	Tape and Reel
2N4401TFR	2N4401	TO-92 3L	Tape and Reel
2N4401TA	2N4401	TO-92 3L	Ammo
2N4401TAR	2N4401	TO-92 3L	Ammo
MMBT4401	2X	SOT-23 3L	Tape and Reel

## Absolute Maximum Ratings<sup>(1),(2)</sup>

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	6.0	V
$I_C$	Collector Current - Continuous	600	mA
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Notes:

1. These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

## Thermal Characteristics

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Max.		Unit
		2N4401 <sup>(3)</sup>	MMBT4401 <sup>(4)</sup>	
$P_D$	Total Device Dissipation	625	350	mW
	Derate Above $25^\circ\text{C}$	5.0	2.8	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	$^\circ\text{C}/\text{W}$

### Notes:

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
4. Device mounted on FR-4 PCB 1.6 inch x 1.6 inch x 0.06 inch.

**Electrical Characteristics**Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage <sup>(5)</sup>	$I_C = 1.0\text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.1\text{ mA}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 0.1\text{ mA}, I_C = 0$	6.0		V
$I_{BL}$	Base Cut-Off Current	$V_{CE} = 35\text{ V}, V_{EB} = 0.4\text{ V}$		0.1	$\mu\text{A}$
$I_{CEX}$	Collector Cut-Off Current	$V_{CE} = 35\text{ V}, V_{EB} = 0.4\text{ V}$		0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain <sup>(5)</sup>	$I_C = 0.1\text{ mA}, V_{CE} = 1.0\text{ V}$	20		
		$I_C = 1.0\text{ mA}, V_{CE} = 1.0\text{ V}$	40		
		$I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$	80		
		$I_C = 150\text{ mA}, V_{CE} = 1.0\text{ V}$	100	300	
		$I_C = 500\text{ mA}, V_{CE} = 2.0\text{ V}$	40		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage <sup>(5)</sup>	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$		0.40	V
		$I_C = 500\text{ mA}, I_B = 50\text{ mA}$		0.75	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage <sup>(5)</sup>	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$	0.75	0.95	V
		$I_C = 500\text{ mA}, I_B = 50\text{ mA}$		1.20	
$f_T$	Current Gain - Bandwidth Product	$I_C = 20\text{ mA}, V_{CE} = 10\text{ V}, f = 100\text{ MHz}$	250		MHz
$C_{cb}$	Collector-Base Capacitance	$V_{CB} = 5.0\text{ V}, I_E = 0, f = 140\text{ kHz}$		6.5	pF
$C_{eb}$	Emitter-Base Capacitance	$V_{BE} = 0.5\text{ V}, I_C = 0, f = 140\text{ kHz}$		30	pF
$h_{ie}$	Input Impedance	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}, f = 1.0\text{ kHz}$	1.0	15.0	$k\Omega$
$h_{re}$	Voltage Feedback Ratio	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}, f = 1.0\text{ kHz}$	0.1	8.0	$\times 10^{-4}$
$h_{fe}$	Small-Signal Current Gain	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}, f = 1.0\text{ kHz}$	40	500	
$h_{oe}$	Output Admittance	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}, f = 1.0\text{ kHz}$	1.0	30	$\mu\text{mhos}$
$t_d$	Delay Time	$V_{CC} = 30\text{ V}, V_{EB} = 2\text{ V}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$		15	ns
$t_r$	Rise Time			20	ns
$t_s$	Storage Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = I_{B2} = 15\text{ mA}$		225	ns
$t_f$	Fall Time			30	ns

**Note:**5. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .

## Typical Performance Characteristics

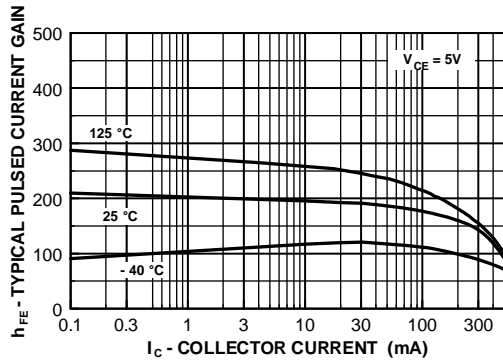


Figure 3. Typical Pulsed Current Gain vs. Collector Current

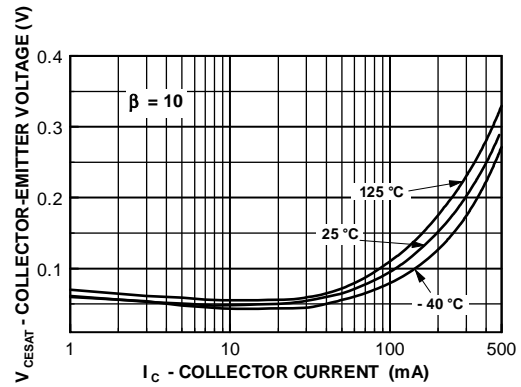


Figure 4. Collector-Emitter Saturation Voltage vs. Collector Current

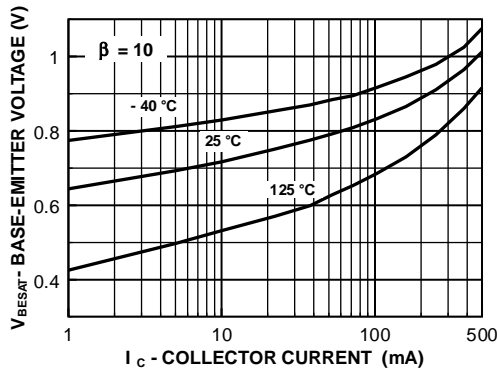


Figure 5. Base-Emitter Saturation Voltage vs. Collector Current

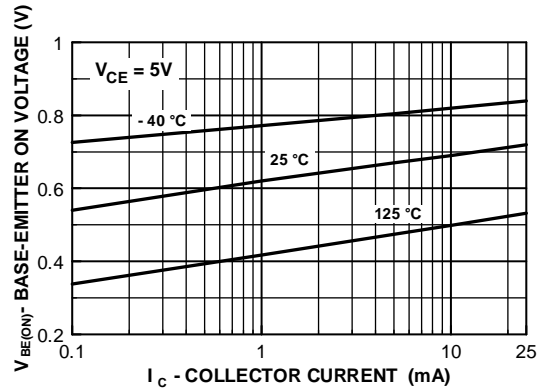


Figure 6. Base-Emitter On Voltage vs. Collector Current

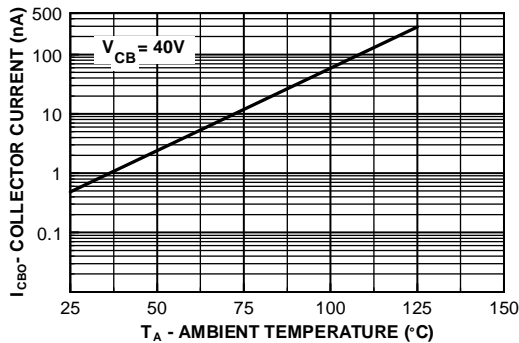


Figure 7. Collector Cut-Off Current vs. Ambient Temperature

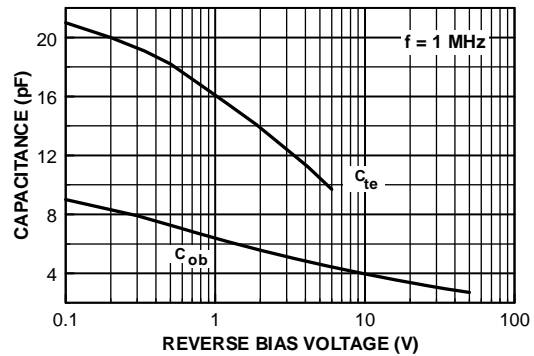


Figure 8. Emitter Transition and Output Capacitance vs. Reverse Bias Voltage

## Typical Performance Characteristics (Continued)

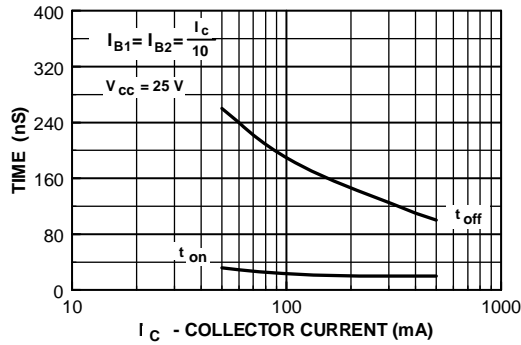


Figure 9. Turn-On and Turn-Off Times vs. Collector Current

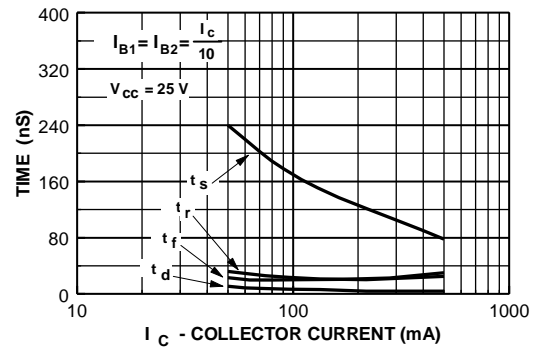


Figure 10. Switching Times vs. Collector Current

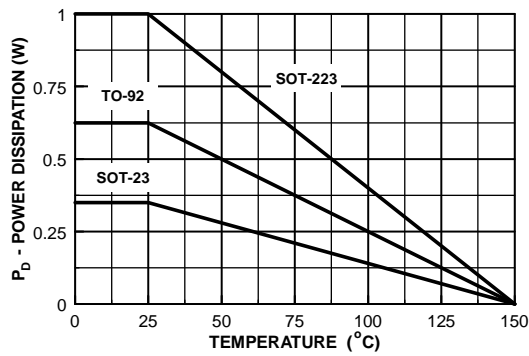


Figure 11. Power Dissipation vs. Ambient Temperature

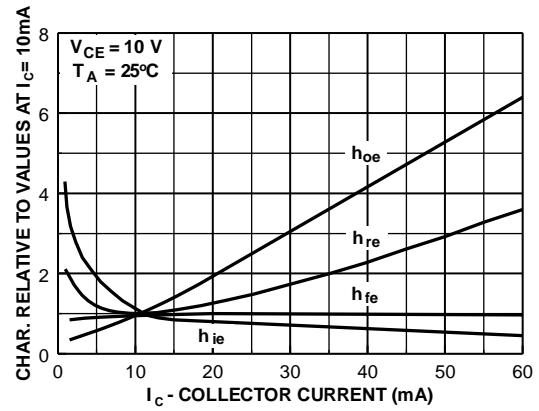


Figure 12. Common Emitter Characteristics

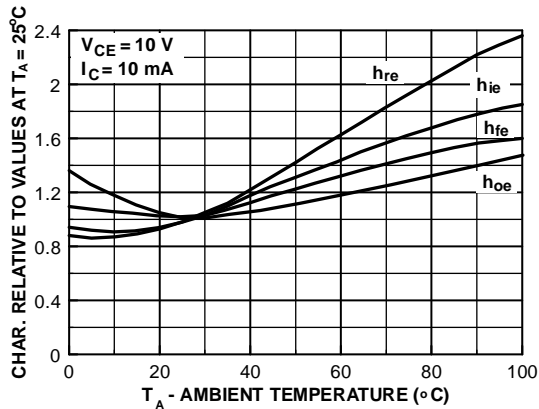


Figure 13. Common Emitter Characteristics

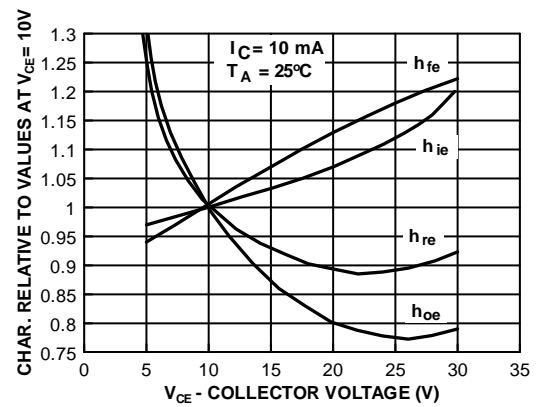
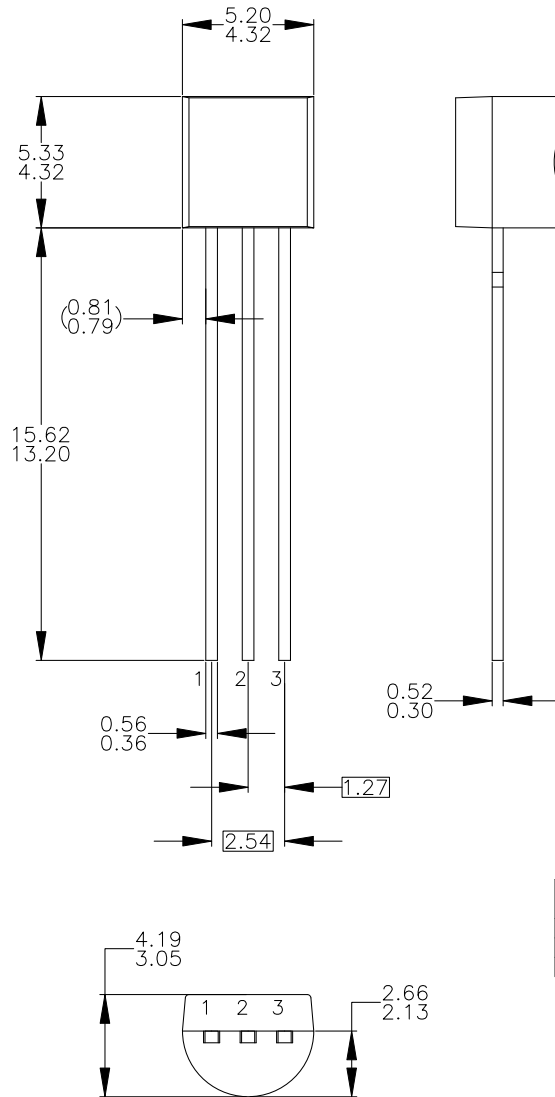


Figure 14. Common Emitter Characteristics

# Physical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994.
- D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92			94			96			97			98		
	P	F	M	P	F	M	P	F	M	P	F	M	P	F	M
1	E	S	S	E	S	S	B	D	G	C	G	D	C	G	D
2	B	D	G	C	G	D	E	S	S	B	D	G	E	S	S
3	C	G	D	B	D	G	C	G	D	E	S	S	B	D	G

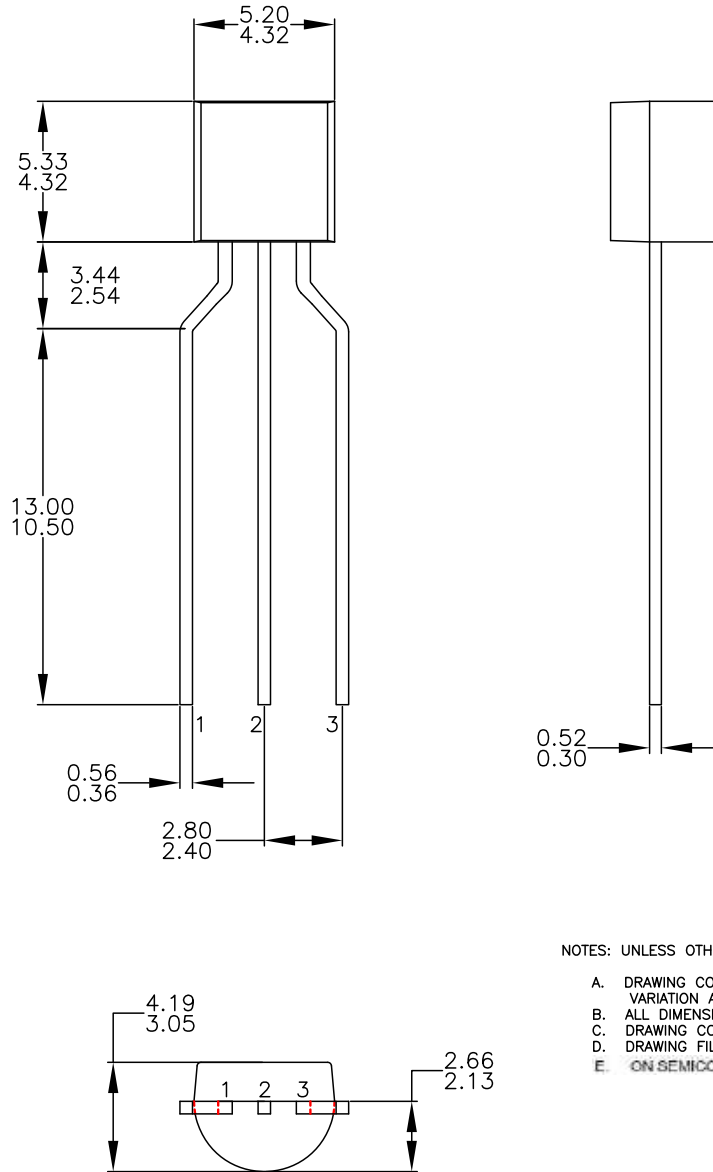
LEGEND:

P — BIPOLAR E — EMITTER D — DRAIN  
F — JFET B — BASE S — SOURCE  
M — DMOS C — COLLECTOR G — GATE

- E) FOR PACKAGE 92, 94, 96, 97 AND 98:  
PIN CONFIGURATION DRAIN "D" AND SOURCE "S"  
ARE INTERCHANGEABLE AT JFET "F" OPTION.
- F) DRAWING FILENAME: MKT-ZA03DREV3.

Figure 15. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

**Physical Dimensions** (Continued)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREVS.
- E. ON SEMICONDUCTOR

**Figure 16. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type**



Physical Dimensions (Continued)

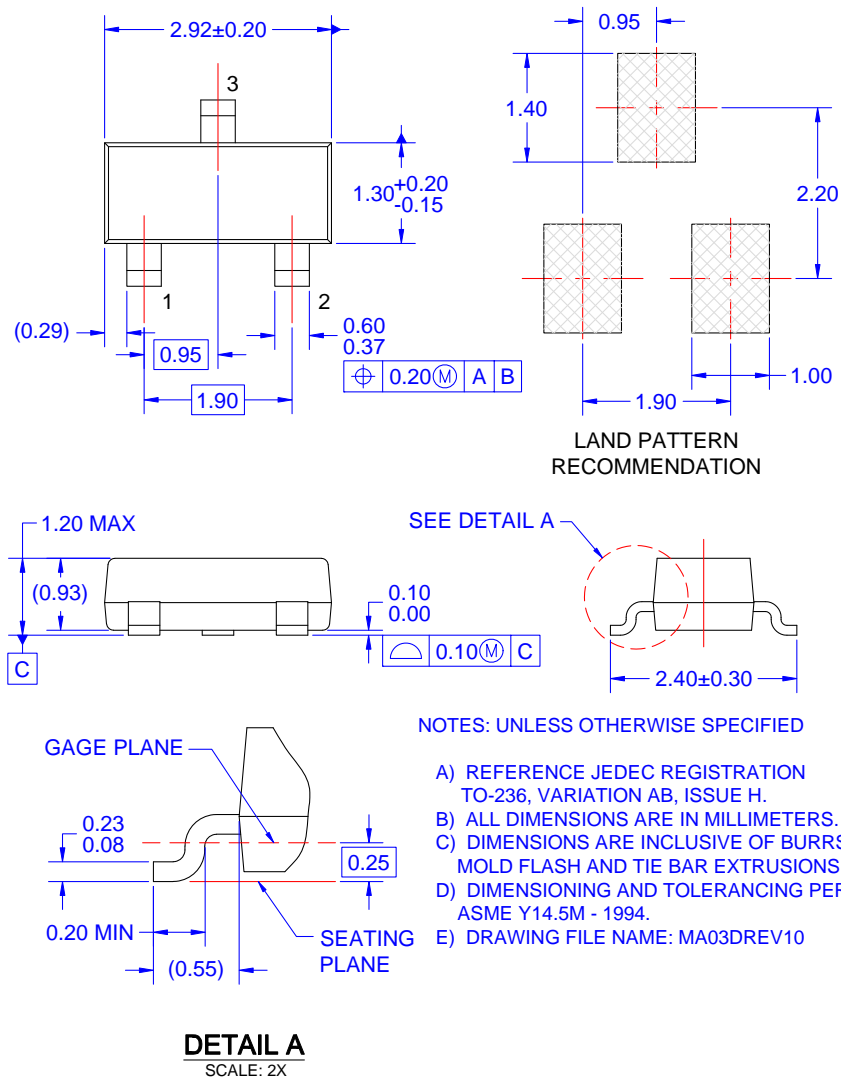



Figure 17. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

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